

ABSTRACT OF THE DISCLOSURE

In a solid-state image-sensing device, when an image sensing operation is performed in each pixel, a MOS transistor T1 is turned on and a MOS transistor T4 is turned off to make a MOS transistor T2 operate in a subthreshold region. When
5 a reset operation is performed in each pixel, the MOS transistor T1 is turned off and the MOS transistor T4 is turned on to feed a constant voltage to the gate and drain of the MOS transistor T2. Then, the MOS transistor T4 is turned off, then the voltage at the node "a" is reset, and then a pulse signal ϕV is fed to a MOS transistor T5 to obtain an output. By using the thus obtained output as
10 compensation data, variations in sensitivity among individual pixels are reduced.